

Title (en)
MICROELECTRONIC STRUCTURE

Title (de)
MIKROELEKTRONISCHE STRUKTUR

Title (fr)
STRUCTURE MICRO-ELECTRONIQUE

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Priority

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- DE 19857039 A 19981210

Abstract (en)
[origin: DE19857039A1] Disclosed is a microelectronic structure comprising a first conductive layer (20, 25) which prevents an oxygen diffusion at said structure. According to the invention, the first conductive layer (20, 25) consists of a base material and at least one oxygen-binding admixture which is provided with at least one element from the fourth subgroup or lanthane group. In a preferred embodiment, the microelectronic structure is used in semiconductor storage components with a metal oxide dielectric as condenser dielectric.

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